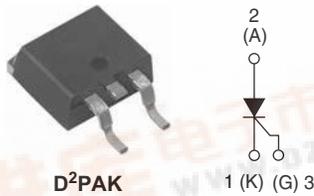




10TTS08SPbF High Voltage Series

Vishay High Power Products

Surface Mountable Phase Control SCR, 10 A



DESCRIPTION/FEATURES

The 10TTS08SPbF High Voltage Series of silicon controlled rectifiers are specifically designed for medium power switching and phase control applications. The glass passivation technology used has reliable operation up to 125 °C junction temperature.



RoHS
COMPLIANT

Typical applications are in input rectification (soft start) and these products are designed to be used with Vishay HPP input diodes, switches and output rectifiers which are available in identical package outlines.

This product has been designed and qualified for industrial level and lead (Pb)-free.

PRODUCT SUMMARY

V_T at 6.5 A	< 1.15 V
I_{TSM}	140 A
V_{RRM}	800 V

OUTPUT CURRENT IN TYPICAL APPLICATIONS

APPLICATIONS	SINGLE-PHASE BRIDGE	THREE-PHASE BRIDGE	UNITS
NEMA FR-4 or G-10 glass fabric-based epoxy with 4 oz. (140 μ m) copper	2.5	3.5	A
Aluminum IMS, $R_{thCA} = 15$ °C/W	6.3	9.5	
Aluminum IMS with heatsink, $R_{thCA} = 5$ °C/W	14.0	18.5	

Note

- $T_A = 55$ °C, $T_J = 125$ °C, footprint 300 mm²

MAJOR RATINGS AND CHARACTERISTICS

PARAMETER	TEST CONDITIONS	VALUES	UNITS
$I_{T(AV)}$	Sinusoidal waveform	6.5	A
I_{RMS}		10	
V_{RRM}/V_{DRM}		800	V
I_{TSM}		140	A
V_T	6.5 A, $T_J = 25$ °C	1.15	V
dV/dt		150	V/ μ s
dI/dt		100	A/ μ s
T_J	Range	- 40 to 125	°C

VOLTAGE RATINGS

PART NUMBER	V_{RRM} , MAXIMUM PEAK REVERSE VOLTAGE V	V_{DRM} , MAXIMUM PEAK DIRECT VOLTAGE V	I_{RRM}/I_{DRM} AT 125 °C mA
10TTS08SPbF	800	800	1.0



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ABSOLUTE MAXIMUM RATINGS					
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES	UNITS
Maximum average on-state current	$I_{T(AV)}$	$T_C = 112\text{ }^\circ\text{C}$, 180° conduction half sine wave		6.5	A
Maximum RMS on-state current	$I_{T(RMS)}$			10	
Maximum peak, one-cycle, non-repetitive surge current	I_{TSM}	10 ms sine pulse, rated V_{RRM} applied, $T_J = 125\text{ }^\circ\text{C}$		120	
		10 ms sine pulse, no voltage reapplied, $T_J = 125\text{ }^\circ\text{C}$		140	
Maximum I^2t for fusing	I^2t	10 ms sine pulse, rated V_{RRM} applied, $T_J = 125\text{ }^\circ\text{C}$		72	A^2s
		10 ms sine pulse, no voltage reapplied, $T_J = 125\text{ }^\circ\text{C}$		100	
Maximum $I^2\sqrt{t}$ for fusing	$I^2\sqrt{t}$	$t = 0.1$ to 10 ms, no voltage reapplied, $T_J = 125\text{ }^\circ\text{C}$		1000	$A^2\sqrt{s}$
Maximum on-state voltage drop	V_{TM}	6.5 A, $T_J = 25\text{ }^\circ\text{C}$		1.15	V
On-state slope resistance	r_t	$T_J = 125\text{ }^\circ\text{C}$		17.3	$m\Omega$
Threshold voltage	$V_{T(TO)}$			0.85	V
Maximum reverse and direct leakage current	I_{RM}/I_{DM}	$T_J = 25\text{ }^\circ\text{C}$	$V_R = \text{Rated } V_{RRM}/V_{DRM}$	0.05	mA
		$T_J = 125\text{ }^\circ\text{C}$		1.0	
Typical holding current	I_H	Anode supply = 6 V, resistive load, initial $I_T = 1$ A		30	
Maximum latching current	I_L	Anode supply = 6 V, resistive load		50	
Maximum rate of rise of off-state voltage	dV/dt	$T_J = 25\text{ }^\circ\text{C}$		150	$V/\mu s$
Maximum rate of rise of turned-on current	dI/dt			100	$A/\mu s$

TRIGGERING					
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES	UNITS
Maximum peak gate power	P_{GM}			8.0	W
Maximum average gate power	$P_{G(AV)}$			2.0	
Maximum peak positive gate current	$+I_{GM}$			1.5	A
Maximum peak negative gate voltage	$-V_{GM}$			10	V
Maximum required DC gate current to trigger	I_{GT}	Anode supply = 6 V, resistive load, $T_J = -65\text{ }^\circ\text{C}$		20	mA
		Anode supply = 6 V, resistive load, $T_J = 25\text{ }^\circ\text{C}$		15	
		Anode supply = 6 V, resistive load, $T_J = 125\text{ }^\circ\text{C}$		10	
Maximum required DC gate voltage to trigger	V_{GT}	Anode supply = 6 V, resistive load, $T_J = -65\text{ }^\circ\text{C}$		1.2	V
		Anode supply = 6 V, resistive load, $T_J = 25\text{ }^\circ\text{C}$		1	
		Anode supply = 6 V, resistive load, $T_J = 125\text{ }^\circ\text{C}$		0.7	
Maximum DC gate voltage not to trigger	V_{GD}	$T_J = 125\text{ }^\circ\text{C}$, $V_{DRM} = \text{Rated value}$		0.2	mA
Maximum DC gate current not to trigger	I_{GD}			0.1	

SWITCHING					
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES	UNITS
Typical turn-on time	t_{gt}	$T_J = 25\text{ }^\circ\text{C}$		0.8	μs
Typical reverse recovery time	t_{rr}	$T_J = 125\text{ }^\circ\text{C}$		3	
Typical turn-off time	t_q			100	



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THERMAL - MECHANICAL SPECIFICATIONS				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum junction and storage temperature range	T_J, T_{Stg}		- 40 to 125	°C
Soldering temperature	T_S	For 10 s (1.6 mm from case)	240	
Maximum thermal resistance, junction to case	R_{thJC}	DC operation	1.5	°C/W
Typical thermal resistance, junction to ambient (PCB mount)	$R_{thJA}^{(1)}$		40	
Approximate weight			2	g
			0.07	oz.
Marking device		Case style D ² PAK (SMD-220)	10TTS08S	

Note

⁽¹⁾ When mounted on 1" square (650 mm²) PCB of FR-4 or G-10 material 4 oz. (140 μm) copper 40 °C/W
For recommended footprint and soldering techniques refer to application note #AN-994

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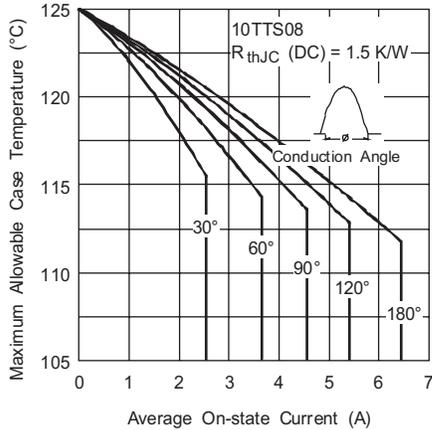


Fig. 1 - Current Rating Characteristics

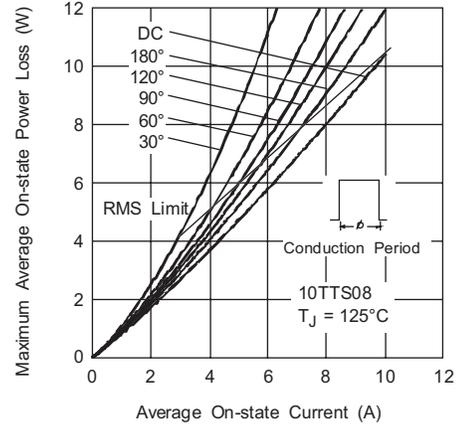


Fig. 4 - On-State Power Loss Characteristics

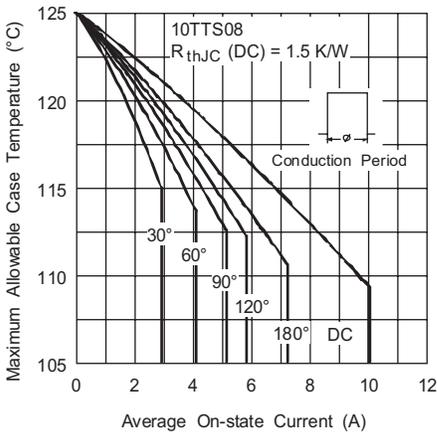


Fig. 2 - Current Rating Characteristics

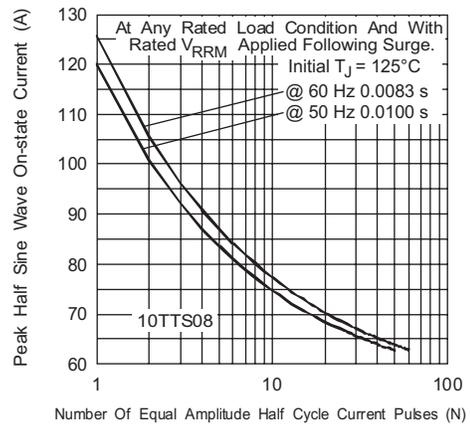


Fig. 5 - Maximum Non-Repetitive Surge Current

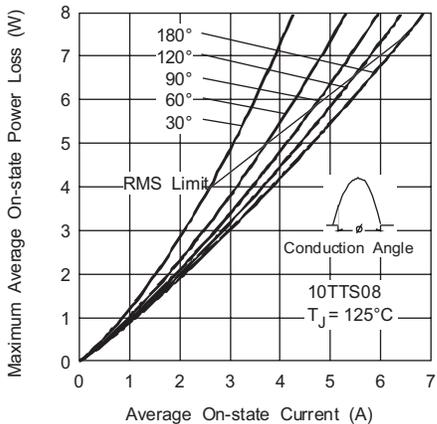


Fig. 3 - On-State Power Loss Characteristics

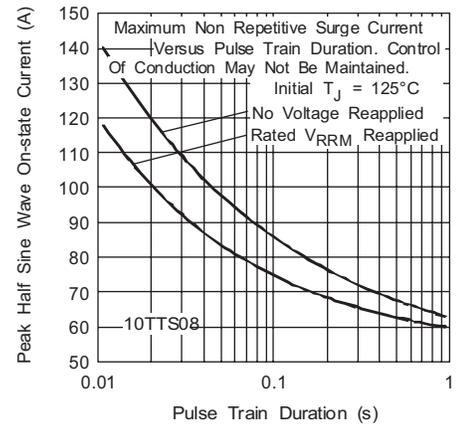


Fig. 6 - Maximum Non-Repetitive Surge Current



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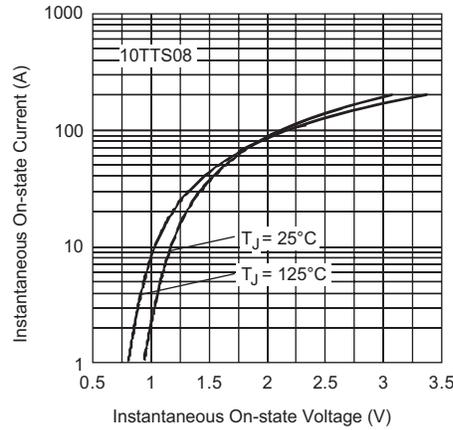


Fig. 7 - On-State Voltage Drop Characteristics

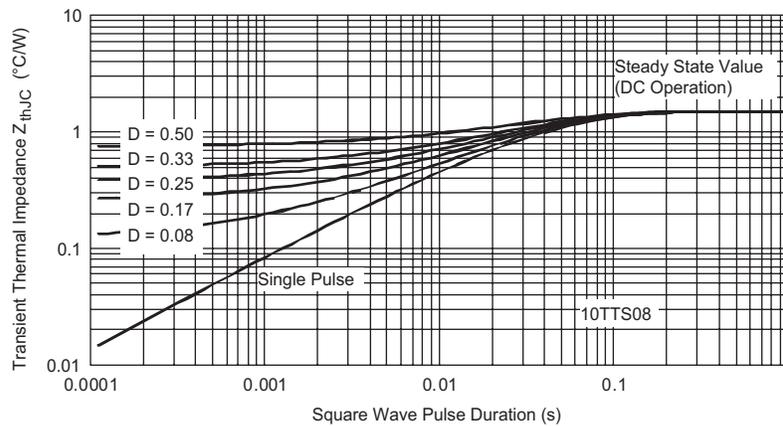


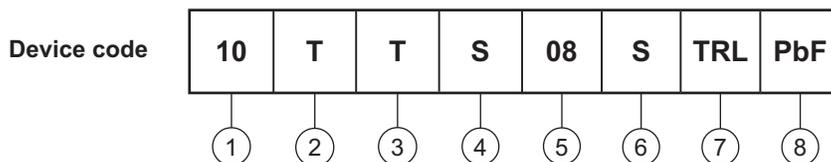
Fig. 8 - Thermal Impedance Z_{thJC} Characteristics

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ORDERING INFORMATION TABLE



- 1** - Current rating, RMS value
- 2** - Circuit configuration:
T = Single thyristor
- 3** - Package:
T = TO-220AC
- 4** - Type of silicon:
S = Converter grade
- 5** - Voltage code x 100 = V_{RRM}
- 6** - S = TO-220 D²PAK (SMD-220) version
- 7** - Tape and reel option:
 - TRL = Left reel
 - TRR = Right orientation reel
- 8** -
 - None = Standard production
 - PbF = Lead (Pb)-free

LINKS TO RELATED DOCUMENTS	
Dimensions	http://www.vishay.com/doc?95046
Part marking information	http://www.vishay.com/doc?95054
Packaging information	http://www.vishay.com/doc?95032



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